

# Specification for Approval

DEVICE NUMBER: BPT-HPG36D-TRB

SAMPLES ATTACHED AREA

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2015.04.22	1.0	1.0	1.0	1.0	1.0	1.0	1.0	1.0		Initial Released

#### FOR CUSTOMER'S APPROVAL STAMP OR SIGNATURE

APPROVED	PURCHASE	MANUFACTURE	QUALITY	ENGINEERING

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**BPT-HPG36D-TRB** 

### Description

- 1. The BPT-HPG36D-TRB is a silicon NPN Phototransistor detector in a1.6x0.8x0.8mm SMD type package.
- 2. This product doesn't contain restriction Substance, comply ROHS standard.

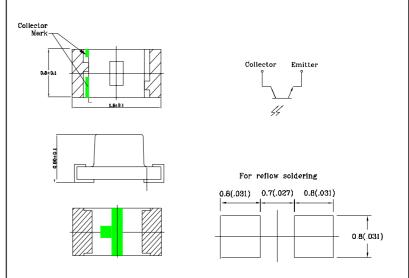
#### Features:

- 1. Wide range of collector current.
- 2. Lend for high sensitivity.
- 3. Low cost plastic package
- 4. Lens Appearance: Water Clear
- This product doesn't contain restriction Substance, comply ROHS standard.

### Applications:

- 1. Smoke Detector
- 2. Automatic Control System
- Any design requiring sensitivity and stable characteristics.

### ●Package Dimensions:



#### NOTES:

- 1.All dimensions are in millimeters (inches).
- 2. Tolerance is ±0.10mm (0.004") unless otherwise specified.
- 3. Specifications are subject to change without notice.

### ■ Absolute Maximum Ratings(Ta=25°C)

Parameter	Rating	Unit
Power Dissipation	75	mW
Collector-Emitter Voltage(Max.)	50	V
Emitter-Collector Voltage(Min.)	5	V
Operating Temperature Range	-40℃~85℃	-
Storage Temperature Range	-40℃~85℃	-
Soldering Temperature	See Page5	-

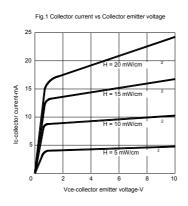


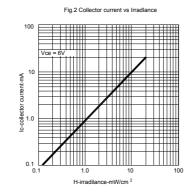
**BPT-HPG36D-TRB** 

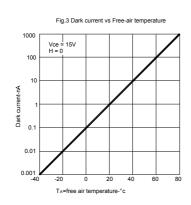
### Electrical and optical characteristics(Ta=25℃)

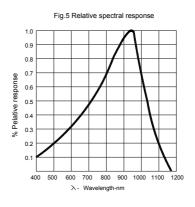
Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Spectrum Sensitivity	λd	I <sub>F</sub> =50mA	500	-	1000	nm
Short Circuit Current	λр	I <sub>F</sub> =50mA	-	940	-	nm
Collector Light Current	$I_{C(ON)}$	V <sub>CE</sub> =5V, λp=940nm, H=1.0mw/cm <sup>2</sup>	1.156	2.398	1	mA
Collector Dark Current	$I_{CEO}$	V <sub>CE</sub> =20V	-	-	100	nA
Rise/Fall Time	Tr/Tf	$V_{CE}$ =5V, Ic=1mA, $R_L$ =1 $K\Omega$	-	15/15	-	us
Viewing Angle	2θ <sub>1/2</sub>	I <sub>F</sub> =50mA -	-	120	-	deg

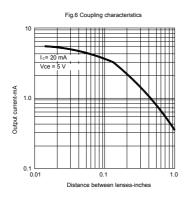
### ■ Typical Electro-Optical Characteristics Curves

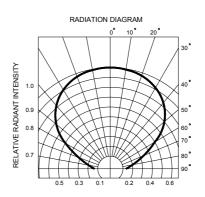








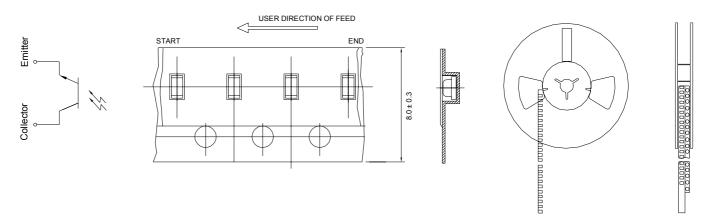




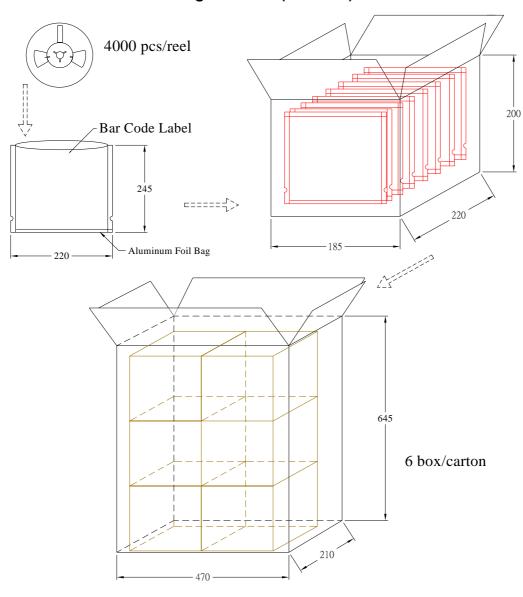


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# Tapping and packaging specifications(Units: mm) Quantity:1000-4000PCS



### ■ Package Method:(unit:mm) Vacuum





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### Bin Limits:

Collector Light Current Bin Limits( $V_{CE}=5V$ , H=1.0mw/cm<sup>2</sup>,  $\lambda$  p=940nm)

DIM 0005	I <sub>C(ON)</sub> (mA)			
BIN CODE	Min	Max		
K	1.156	1.665		
L	1.665	2.398		
М	2.398	3.455		
N	3.455	4.976		

Tolerance for each Bin limit is  $\pm$  15 %

● BIN:	<u>X</u>
	<u>†</u>
	Collector Light Current Bin Code



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### Reliability Test

Classification	Test Item	Reference Standard	Test Conditions	Result
	Operation Life	MIL-STD-750D:1026 MIL-STD-883D:1005 JIS-C-7021 :B-1	Ta: Under room temperature Test time:1,000hrs IF=Product Recommended IF	0/32
Endurance		MIL-STD-202F:103B JIS-C-7021 :B-11	Ta:85±5℃ RH:90%-95% Test time:240hrs	0/32
Test	High Temperature Storage	MIL-STD-883:1008 JIS-C-7021 :B-10	Ta:100±5℃ Test time:1,000hrs	0/32
	Low Temperature Storage	JIS-C-7021 :B-11	Ta: -40±5°C Test time=1,000hrs	0/32
Environmental Test	Temperature Cycling	MIL-STD-202F:107D MIL-STD-750D:1051 MIL-STD-883D:1010 JIS-C-7021 :A-2	Ta:-35±5 °C ~25±5 °C ~85±5 °C ~25±5 °C 30min 5min 30min 5min	0/32
	Thermal Shock	MIL-STD-202F:107D(1980) MIL-STD-750D:1051(1995) MIL-STD-883D:1011(1991)	Ta:-40±5°C ~+85±5°C 10min 10 min Time: 20min/cycle 10cycle	0/32
	Wetting balance	MIL-STD-883:2003 MIL-STD-202F:208D MIL-STD-883D:2003	Ta:230±5°ℂ Time:5±0.5s	0/32
	Solder Resistance	MIL-STD-202F:210A MIL-STD-883D:1011 JIS-C-7021 :A-1	Ta:260±10°C Time:10±1s	0/32

### Judgment criteria of failure for the reliability

Measuring items	Symbol	Measuring conditions	Judgement criteria for failure	
Forward voltage	$V_{F}(V)$	I <sub>F</sub> =5mA	Initial Level*1.1	
Reverse current	$I_R(uA)$	V <sub>R</sub> =5V	Over U*2	
Luminous intensity	lv ( mcd )	I <sub>F</sub> =5mA	Initial Level*0.7	

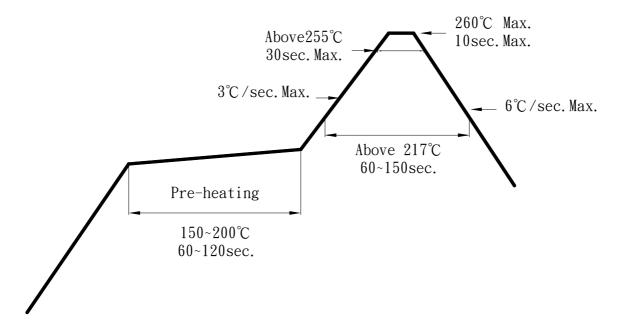
Note: 1.U means the upper limit of specified characteristics.

2.Measurment shall be taken between 2 hours and after the test pieces have been returned to normal ambient conditions after completion of each test.



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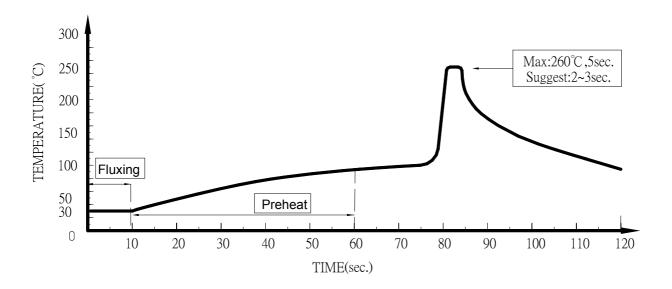
### ●IR-Reflow Soldering



- 1. Avoid any external stress applied to the resin while the LEDs are at high temperature, especially during soldering.
- 2. Avoid rapid cooling or any excess vibration during temperature ramp-down process
- Although the soldering condition is recommended above, soldering at the lowest possible temperature is feasible for the LEDs

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### Dip Soldering



- Please avoid any external stress applied to the lead-frames and epoxy while the LEDs are at high temperature, especially during soldering
- 2. DIP soldering and hand soldering should not be done more than one time.
- 3. After soldering, avoid the epoxy lens from mechanical shock or vibration until the LEDs are back to room temerature.
- 4. Avoid rapid cooling during temperature ramp-down process
- 5. Although the soldering condition is recommended above, soldering at the lowest possible temperature is feasible for the LEDs

#### IRON Soldering

300 $^{\circ}$  Within 3 sec.,One time only.



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### Notes for designing:

Care must be taken to provide the current limiting resistor in the circuit so as to drive the BRIGHT LEDs within the rated figures. Also, caution should be taken not to overload BRIGHT LEDs with instantaneous voltage at the turning ON and OFF of the circuit.

When using the pulse drive care must be taken to keep the average current within the rated figures. Also, the circuit should be designed so as be subjected to reverse voltage when turning off the BRIGHT LEDs.

### Storage:

In order to avoid the absorption of moisture, it is recommended to solder BRIGHT LEDs as soon as possible after unpacking the sealed envelope.

If the envelope is still packed, to store it in the environment as following:

- (1) Temperature :  $5^{\circ}$ C  $30^{\circ}$ C ( $41^{\circ}$ F)Humidity : RH 60% Max.
- (2) After this bag is opened, devices that will be applied to infrared reflow, vapor-phase reflow, or equivalent soldering process must be:
- a. Completed within 168 hours.
- b. Stored at less than 30% RH.
- (3) Devices require baking before mounting, if: (2) a or (2) b is not met.
- (4) If baking is required, devices must be baked under below conditions: 48 hours at  $60^{\circ}\text{C} \pm 3^{\circ}\text{C}$ .

### Package and Label of Products:

- (1) Package: Products are packed in one bag of 4000 pcs (one taping reel) and a label is attached on each bag.
- (2) Label:

